

Thermodynamic, thermoelectric and magnetic properties of FeSb₂ : A combined first principles and experimental study

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We analyze the thermodynamic, magnetic and transport properties of the narrow band gap semiconductor FeSb₂ using density functional theory calculations corroborated by nuclear inelastic spectroscopy and ultrasound experiments. The vibrational properties (phonon spectrum, density of states, heat capacity) and elastic constants are computed through response function calculations and are in good agreements with the measurements. The electron-phonon coupling effects are also studied. The estimations of linewidth broadening due to electron-phonon coupling, along the high symmetry directions in the first Brillouin zone are given. The linewidth broadening reaches the largest value for Fe optical modes in the vicinity of the $X[0.5, 0, 0]$ point. The broadening, when compared to those obtained at the other symmetry points, differ by up to two orders of magnitude. From the Boltzmann theory applied to our electronic band structure we investigate the electrical transport properties. It is found that a purely electronic structure description is incompatible with the record value of the Seebeck coefficient experimentally observed at $T \approx 12$ K. The diamagnetic to paramagnetic crossover at a temperature around 100 K is also described from the calculation of the magnetic susceptibility and results compare well with experiment.

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I. INTRODUCTION

The study of the thermodynamic, thermoelectric, and magnetic properties of iron diantimonide FeSb₂ has been the subject of intense research investigations¹⁻⁴. The particular interest in this materials is due to its interesting low temperature physical properties and the considerable potential applications, the most promising of which is in the development of cryo-refrigeration, because of its large thermoelectric power at low temperature⁴.

FeSb₂ crystallizes in the loellingite (orthorhombic marcasite type) structure with Fe ions surrounded by deformed Sb octahedra⁵ and contains two formula units per unit cell. The low temperature state is semiconductor with an extremely narrow indirect band gap which promotes strong correlation effects between d and conduction band states⁶⁻⁹. The minimum direct gap value extracted from reflectivity measurements^{10,11} range between 30 and 40 meV. Recent band structure calculations¹² have shown that it is possible to properly describe the indirect semiconducting gap of FeSb₂ by going beyond standard DFT methods for instance using GW calculations. The physical properties of FeSb₂ are similar in many respects to those of iron silicide FeSi^{13,14}. The most

remarkable observed similarities are the temperature-dependent magnetic susceptibility^{15,16} $\chi(T)$ and the strong anisotropic electrical transport properties¹⁷⁻¹⁹. For a magnetic field applied along the c -axis, the system evolves from a diamagnetic state towards a paramagnetic state through a crossover temperature at about 100 K. The electrical resistivity exhibits a semiconducting behavior along the a and c axis whereas, for the b axis, a semiconducting-metallic crossover temperature of 40K is observed. Among the open questions regarding the temperature dependence of the physical properties of FeSb₂, most attention has recently been focused on the origin of the huge low temperature thermopower. Of particular interest is the issue of whether the thermopower is purely electronic, as is usually assumed, or if there are some other important effects due to phonon drag²⁰ for instance. The physical origin of this phenomenon is in fact not yet clarified. Adding to properties observed earlier, Bentien et al.²¹ recently found that FeSb₂ exhibits a record Seebeck coefficient $S \approx -45000 \mu\text{V K}^{-1}$ at $T \approx 12$ K, and the thermoelectric power factor $PF = S^2 \cdot \rho^{-1}$, where ρ represents the electrical resistivity, can reach a value of $\approx 2300 \mu\text{WK}^{-2}\text{cm}^{-1}$. This value is 65 times larger than the reference value measured for Bi₂Te₃-based

thermoelectric materials. However the figure of merit $ZT = S^2 \cdot \rho^{-1} \kappa^{-1} T$ is rather low, due to the large value of the thermal conductivity¹² $\kappa = 250 \text{ WK}^{-1} \text{ m}^{-1}$ at $T \approx 12 \text{ K}$.

Herein, we combine experimental and theoretical investigation of transport, magnetic and vibrational properties of FeSb₂. We analyze the transport coefficients within an electronic structure picture where the contribution of the lattice thermal conductivity κ_L to ZT is neglected (low temperature approximation). Because the electrical transport properties of narrow band gap semiconductors are very sensitive to chemical substitution²², we have investigated the effect of donor impurity doping on the Seebeck coefficient. The exponentially-activated paramagnetic susceptibility²³ with increasing temperature is highlighted. Regarding the vibrational properties, few studies have been performed so far^{24,25}, and the results were presented from the point of view of its absorption spectrum in comparison with those obtained in FeSi, which has similar physical properties^{10,18}. This restriction does not allow a more detailed description of some physical properties, such as the lattice vibrations and their interaction with electrons, which are necessary to understand the mechanism governing the low temperature thermoelectric power of FeSb₂. The experimental phonon density of states, sound velocities and shear modulus were obtained by nuclear inelastic scattering, and resonant ultrasound spectroscopy measurements. Results are presented in comparison with those calculated using methods based on response function calculations²⁶.

II. METHODS

A. Computational methods

The calculations were carried out using the density functional theory^{27,28} and norm-conserving pseudopotentials (including spin-orbit corrections²⁹ for Sb) in the generalized gradient approximation as implemented in the ABINIT package³⁰. Details of our calculation are as follows. The exchange-correlation potential is in the form of Perdew-Burke-Ernzerhof (PBE)³¹. We use a plane wave basis set with a kinetic energy cutoff of 45 Ha. For the atomic positions relaxation, we sample the entire Brillouin zone (BZ) with $16 \times 16 \times 16$ k points corresponding to 2097 k points in the irreducible Brillouin zone (IBZ). The BZ integrations were performed using a Gaussian smearing method with a width of 2.7 meV. The total energy is converged to within 3×10^{-4} meV and the obtained equilibrium structure is of loellingite type, with an orthorhombic cell. The calculated lattice parameters are $a=5.83 \text{ \AA}$, $b=6.50 \text{ \AA}$ and $c=3.16 \text{ \AA}$. These results are consistent with experimental values³. In order to compute the transport properties and electron-phonon interaction properties we need a finer k-point grid. The electronic eigenvalues and phonon eigenfrequencies were determined on a grid consisting of $24 \times 24 \times 24$ k vectors

and $4 \times 4 \times 4$ phonon wave vectors. The phonon density of states and dispersion along high symmetry lines have been obtained by standard methods based on response function calculations²⁶. We considered perturbations in the high-symmetry directions of the crystallographic cell. The resulting thermodynamic properties (the vibrational entropy and heat capacity) were calculated using quasi-harmonic approximation^{32,33}. The calculation of transport properties was performed using a denser mesh of 450000 k points of the BZ. The semi-classical Boltzmann theory as implemented in the transport code BoltzTrap³⁴ has been used to compute the electrical transport coefficients and the magnetic susceptibility. We point out that there is no alternative magnetic solution for the ground state of FeSb₂, in agreement with experiment¹⁷.

B. Experimental methods

The sample enriched with ⁵⁷Fe was made from finely ground powder of pure elements. The powders were mixed thoroughly before they were placed in a corundum crucible and sealed in vacuum in a quartz tube. The elements were allowed to react for 1 week at 730°C. The sample was pure with the measured resolution obtained by a Bruker D8 Advanced equipped with CuK α 1 and an energy dispersive Sol-X detector. The sample for the resonance ultrasound spectroscopy was a non-enriched sample prepared in a similar way followed by spark plasma sintering pressing. A pellet was pressed by heating to 600°C in 5 min at 60 MPa and held at 600°C for 10 min. Before pressing a small impurity of Sb was observed by x-ray diffraction, after pressing a tiny amount of Fe was observed, however the content was too small for quantitative refinements.

The partial density of phonon states (DPS) of Sb and Fe were obtained by nuclear inelastic scattering (NIS) measurements. The technique and the extraction of the DPS from the NIS spectra is explained in Ref.³⁵⁻³⁷. The measurements with the ⁵⁷Fe and the ¹²¹Sb resonance took place on the 95% ⁵⁷Fe enriched powder sample at the ESRF ID18 and ID22N beamlines, respectively, in 16 bunch mode, and at 50 and 67 K, respectively, in order to reduce the multiphonon contributions. The resolution was 0.7 and 1.3 meV FWHM for measurements with the ⁵⁷Fe and ¹²¹Sb resonance, respectively.

The resonant ultrasound spectroscopy, RUS, response was measured with a homemade inset for a QD-PPMS. The measurements were done on a polished $2.205(2) \times 2.118(2) \times 1.784(2) \text{ mm}^3$ polycrystalline sintered powder sample upon cooling between 300 and 10 K. It was verified by Laue diffraction that the sample is polycrystalline. The density of the sample was $\sim 98\%$ of the x-ray density. Only 20 resonance frequencies could be reliably determined and modeled using a finite element algorithm for a rectangular parallelepiped with a 10th order polynomial fit for the displacements³⁸. The root mean square deviation of the fits was of $\sim 0.8\%$, *i.e.* somewhat large.

A too small number of resonance lines had a significant c_{11} contribution, thus it can not be reliably determined. The temperature dependence of the c_{44} component was obtained through fits and then verified by the temperature variation of particular resonance frequencies which depend by more than 95% on c_{44} . The weakness in the modeling likely comes from texture in the sample caused by the sintering process.

III. RESULTS AND DISCUSSIONS

A. Electronic band structure

The GGA electronic band structure is displayed in Fig. 1. The maximum of the valence band is at the $R[0.5, 0.5, 0.5]$ point and the minimum of the conduction band is found in the line between the points Γ and $Z[0\ 0\ 0.5]$. The semiconducting optical gap was estimated at

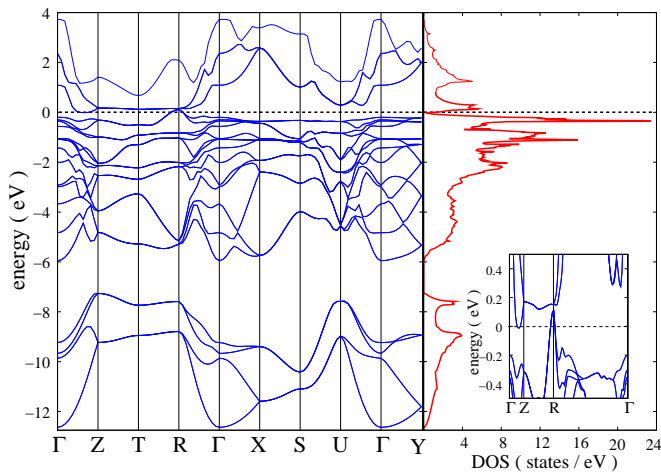


FIG. 1: Calculated electronic band structure and density of states of FeSb₂ using GGA. The red dotted line indicates the Fermi level. The inset right figure shows the small direct band gap at the R [0.5,0.5,0.5] point (corner of the first Brillouin zone), and the overlap between the maximum of the valence band which is located at R point and the minimum of the conduction band lying between the Γ and Z [0 0 0.5] points.

35 meV from reflectivity measurements¹⁰, this is consistent with the calculated direct gap of 33 meV, despite the well known underestimation of the band gap within DFT, see right inset to Fig. 1. The density of states in the vicinity of the Fermi level is largely dominated by the Fe- d states, however a substantial contribution from the Sb- p states is observed. The projected DOS show that the two major peaks at the top of the valence band and the bottom of the conduction band have mainly d_{z^2} and $d_{x^2-y^2}$ characters⁴. These two enhanced narrow bands and the small band gap suggest strong electronic correlation effects that may be responsible for the magnetic and transport anomalies in FeSb₂ at low temperature.

B. Magnetic susceptibility

The study of the magnetic susceptibility reveals an interesting diamagnetic to paramagnetic transition at temperature around 100 K, as experimentally observed²³. Fig. 2 displays the magnetic susceptibility χ as a function of temperature. The magnetic susceptibility is calculated from the electronic density of states $g(\epsilon)$ (Fig. 1 right panel) and the derivative of the Fermi distribution function $f(\epsilon, \mu, T_e)$ with respect to energy,

$$\chi = -2\mu_o\mu_B^2 \int g(\epsilon)(\partial f(\epsilon, \mu, T_e)/\partial \epsilon)d\epsilon + \chi_0 \quad (1)$$

where μ_o and μ_B are the magnetic permittivity of vacuum and the Bohr magneton, respectively. The calculation of the derivative $\partial f(\epsilon, \mu, T_e)/\partial \epsilon$ requires the knowledge of the chemical potential μ as a function of electronic temperature, which is evaluated from the conservation of total electrons number $N_e = \int g(\epsilon)f(\epsilon, \mu, T_e)$. $\chi_0 = -4.510^{-5}$ emu/mol is an additional constant term due to the core diamagnetism³. Below 40 K χ is tem-

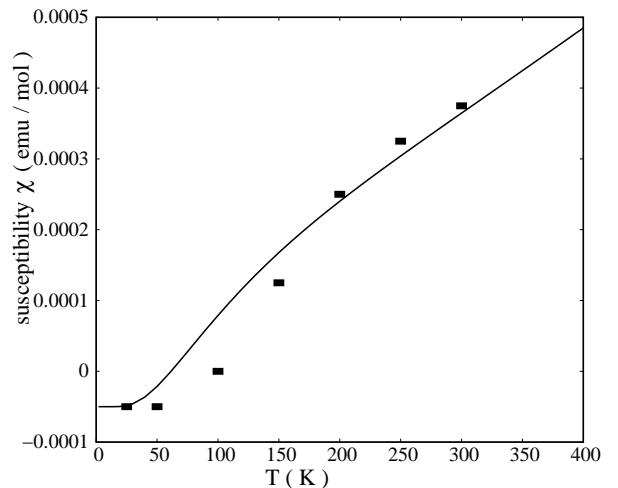


FIG. 2: The temperature evolution of the magnetic susceptibility compared with experimental extracted from Ref.³. χ evolves from a constant value = -4.510^{-5} emu/mol at low temperatures (diamagnetic region) towards positive values (paramagnetic region) above $T=80$ K.

perature independent. The diamagnetism ($\chi < 0$) is progressively reduced with rising temperature leading to the paramagnetic behavior above 80 K ($\chi > 0$). The small crossover temperature, $T \approx 80$ K is attributed to the narrow band gap. FeSb₂ can be presented as a Kondo insulator system where the electronic structure is characterized by two dominant bands at the vicinity of the Fermi level (see Fig. 1), with a given width of W , separated by a gap. Raising the temperature leads to delocalization of electrons from lower bands to upper bands and activates the Pauli magnetic susceptibility³ as shown in Fig. 2. The same scenario has been found to be the underlying mechanism of phase changes observed in the related system FeSi¹⁰.

C. Transport properties

As previously mentioned, the calculation of transport coefficients was performed by using the semiclassical Boltzmann theory applied to the GGA electronic band structure described in Sec. III A.

1. *Seebeck coefficient.* Fig. 3 shows the Seebeck coefficient S as function of temperature. A spectacular drop is observed at low temperatures, yielding a minimum value of $S_{max} \approx -800 \mu\text{V K}^{-1}$ at $T \approx 15$ K. The enhanced peak is followed by a rapid increase of S with T towards positive values above $T \approx 25$ K. Whereas a fairly good agreement is obtained with experimental results³⁹, S_{max} is rather different from the record value $S_{max} \approx -45000 \mu\text{V K}^{-1}$ measured by Bienten et al²¹, along the c -direction. Our calculations also show that S is relatively larger in the c than in the a or b direction. The directional dependence of S is not given here. However, the

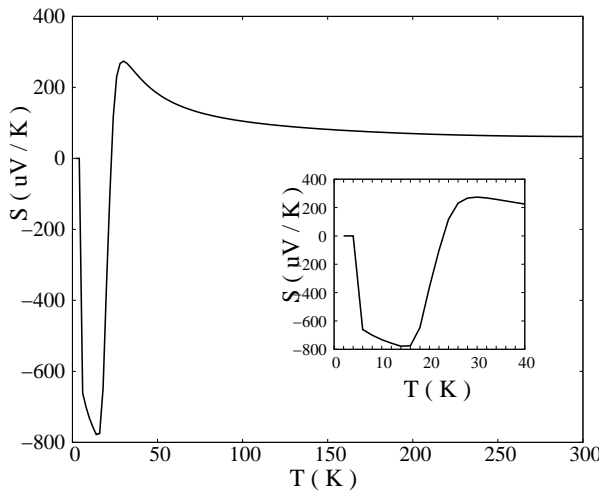


FIG. 3: Seebeck coefficient S vs. temperature T . The inset shows the low temperature curve between 0 and 40K for S .

observed record value of $S(T)$ can not be quantitatively reproduced by a purely electronic structure picture, or by a classical description of electron diffusion in non degenerate system⁴⁰. This implies that other contributions must be present. Although many aspects may suggest that the phonon drag effect²⁰ plays a dominant role in the large enhancement of S at $T \approx 12$ K, it was also shown in a comparative study⁴⁰ on related systems such as RuSb_2 that the role of phonon drag is minor.

2. *Donor doping.* The quality of the sample used for experimental measurements is known to have a large influence on the value of S_{max} . The measured values of S_{max} depend on the purity of the polycrystal, similar measurements⁴ with a less pure polycrystal; have led to much smaller values.

Our observations indicate that S is very sensitive to the value of the chemical potential μ as is shown in Fig.4. The value of μ depends on the concentration of charge carriers and hence on the purity of the material. In the

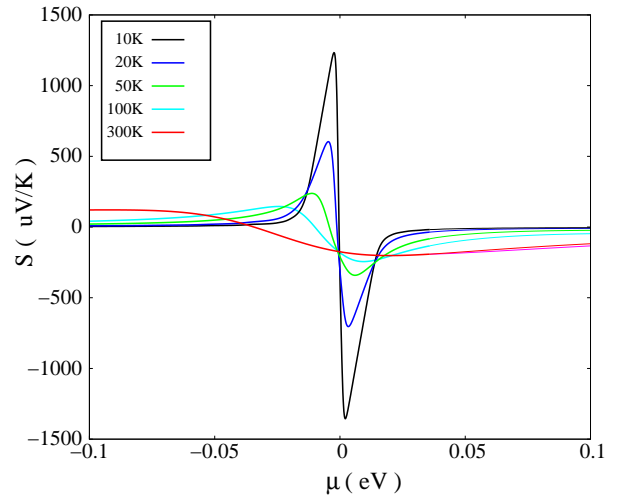


FIG. 4: Seebeck coefficient S vs. chemical potential μ at different temperatures. S is very sensitive to small changes in μ .

intrinsic case where the number of electrons excited to the conduction band, n , is equal to the number of holes p , left behind, the chemical potential is $\mu \approx \Delta/2 + (3/4)k_B T \ln(m_h/m_e)$, where m_h and m_e are respectively the effective masses of holes and electrons. In this regime μ is displaced from the middle of the band gap by a term that depends on temperature and the ratio of the effective masses. The point of charge neutrality at $T=0$ K is very close to the midgap point. For non-zero temperatures, the donor and acceptor sites can be thermally ionized. In the extrinsic case for finite dopings the charge neutrality condition $n + N_a^- = p + N_d^+$ governs the carrier concentration, where $N_a^- = N_a(1 - f(\Delta - E_a))$ and $N_d^+ = N_d(1 - f(\Delta - E_d))$ are the concentration of ionized acceptors and donors. N_a and N_d are the number of acceptors and donors, E_a and E_d the corresponding energy levels and f the Fermi function.

In the presence of donor impurities $n = p + N_d^+$ corresponding to $\mu > 0$ and $S < 0$ in Fig.4, the chemical potential is $\mu = (\Delta/2 - E^{imp}/2) - k_B T \ln(n/N_d^+)$, where $E^{imp} = \Delta/2 - E_d$ is the impurity activation energy. The enhancement of the Seebeck coefficient at a given temperature depends on whether the additional carriers bring μ towards its optimal value μ_{opt} or not. We found $\mu_{opt} = 0.21$ meV for $T=16$ K corresponding to a carrier density of $n = 3.2 \times 10^{15}/\text{cm}^3$. This optimum chemical potential which maximizes S is located above the midgap point. The optimum carrier density found in Ref.¹² corresponds to $n = 1.3 \times 10^{16}/\text{cm}^3$ at $T=220$ K. It appears therefore that the combination of an optimal doping and small resistivity allows to maximize the thermopower S .

3. *Resistivity.* Fig. 5 shows the variation of the electrical resistivity ρ with temperature. $\rho(T)$ is evaluated assuming a temperature-independent relaxation time τ of electrons. For the estimation of τ , we fit the experimental data reported in Fig. 2 of Ref.⁴⁰ by adjusting the

value of ρ at low temperature. We find $\tau = 0.225$ ps. A step further towards a complete theoretical description of the transport properties is to go beyond the constant relaxation time approximation by taking into account the anisotropic nature of the electron scattering by phonons and the temperature dependence of τ .

Below $T=400$ K, the resistivity exhibits a semiconducting behavior with two different regions separated by a plateau at $T \approx 20$ K and is similar to what is observed in Ref.^{4,21}. The activation energy above 50 K obtained by fitting the Arrhenius equation $\rho(T) = \rho_0 \exp(E_a/2k_B T)$ is estimated to $E_A \sim 350$ -450 K in agreement with experimental measurements⁴⁰. Furthermore, it appears from our calculations that the low-temperature resistivity is highly anisotropic. Along the c axis we observe a large increase of $\rho(T)$ values, in agreement with experimental measurements¹⁷.

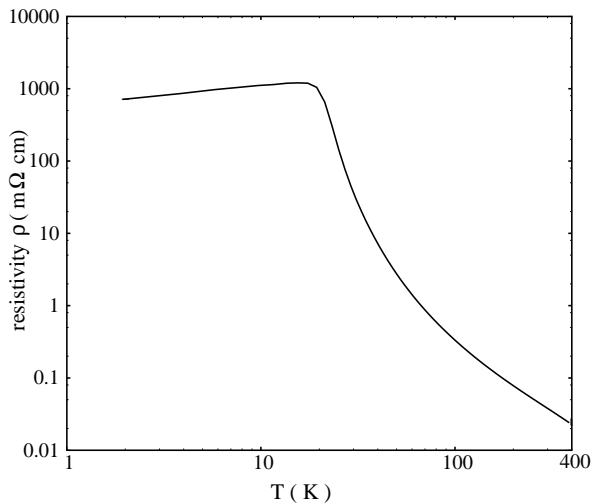


FIG. 5: Calculated electrical resistivity ρ vs. temperature in a logarithmic scale. $\rho(T)$ is computed using a constant relaxation time $\tau=0.225$ ps for the whole temperature range.

The efficiency of thermoelectric materials is determined by the value of the figure of merit ZT defined above. The reference value measured for Bi_2Te_3 -based thermoelectric material is $ZT=0.9$ ⁴¹. A target value larger than 2 is desirable for a large-scale applications. From the definition of ZT , it clearly appears that systems with large thermoelectric power must be both good electrical conductor and very limited in terms of heat conduction, to have a maximum ZT . It is therefore necessary to find a way to separate the electrical and thermal properties in order to maximize ZT , *i.e.* to obtain high values of the Seebeck coefficient S and low value of the electrical resistivity ρ while minimizing the lattice thermal conductivity κ .

D. Phonons and elastic constants

1. Density of states. The calculated partial DPS, $g(E)$,

	Theo.		Exp.	
	Fe	Sb	Fe	Sb
v_s (m/s)	3300(50)	3250(50)	3050(50)	3000(100)
F^m (N/m)	175(5)	150(5)	163(5)	165(5)
θ_D (K)	447(5)	276(5)	405(5)	270(10)

TABLE I: The thermodynamic properties obtained from the partial DPS at $T = 50$ K.

and the DPS obtained from NIS are in good agreement, see Fig. 6. The phonon modes related to Sb are mainly below ~ 23 meV, whereas the iron modes are in a higher energy range above ~ 23 meV. There is a small contribution of Sb modes in the high energy range and of Fe modes in the low energy range, which is due to the interaction of Sb and Fe modes. The Sb modes have a similar shape than the Sb modes in the skutterudite FeSb_3 ³⁷, but the thermodynamic properties, such as the velocity of sound and the Debye temperature in these compounds, are different, as the Fe modes here are in a larger energy range. The experimental Sb phonons are very well reproduced by the calculation. In contrast, for the Fe phonons, although the shape is very well reproduced, the experimental modes are somewhat softer than calculated ones, which might be indicative of some significant softening due to electron phonon interactions already at 50 K. The Debye level can be obtained from the low energy range in the reduced DPS, $\lim_{E \rightarrow 0}(g(E)/E^2)$, see inset to Fig. 6. From the Debye level, the velocity of sound, v_s , can be obtained by $\lim_{E \rightarrow 0}(g(E)/E^2) = M_R/(2\pi^2 \rho \hbar^3 v_s^3)$, with the mass of the resonant atom, M_R , and the density of the material ρ . The mean values of v_s obtained from the calculated and experimental Fe DPS are 3300(50) and 3050(50) m/s, respectively, in good agreement with the v_s obtained by the measured Sb DPS, see Table I. The difference between the calculated and experimental velocity of sound can be partly explained by differences in temperature, because the experimental DPS was obtained at a finite temperature of 50 K. The partial velocity of sound, v_λ , along the longitudinal and transversal directions are obtained from the calculated phonon dispersion curves using the acoustic approximation, see Table II. The DPS also gives reliable and direct access to the element-specific mean force constants both for Fe³⁵ and for Sb⁴² by the relation $F^m = M_R/\hbar \int_0^\infty g(E)E^2 dE$. The obtained F^m values for Fe and Sb from calculation and experiment are in good agreement, see Table I. The element-specific Debye temperatures can be obtained from the DPS with the relation $\theta_D^2 = 3/(k_B^2 \int_0^\infty g(E)dE/E^2)$, obtained in the high temperature limit, see Ref.³⁵. The obtained calculated and experimental values are in agreement, see Table I.

2. *Elastic constants.* The polycrystalline average of the c_{44} shear modulus exhibits first softening with increasing temperature up to 120 K, which is the typical behavior observed in most materials, see Fig. 7. However, above 120 K hardening with increasing temperature is observed, which correlates with the onset of the grad-

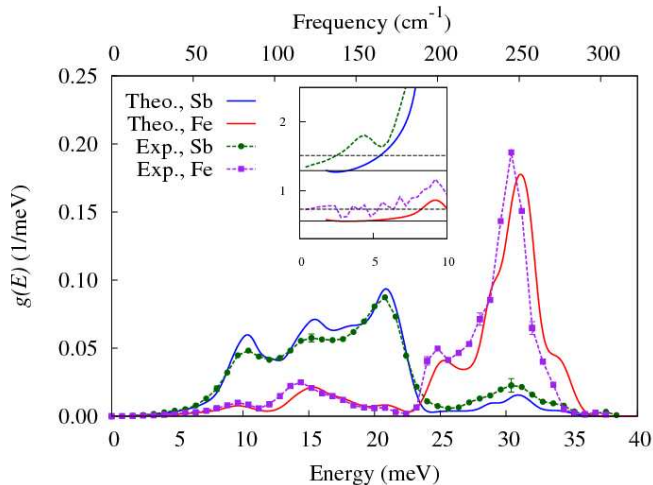


FIG. 6: Comparison of the DPS obtained by calculation, Theo., and by NIS, Exp., measured with the ^{57}Fe resonance at 50 K and with the ^{121}Sb resonance at 67 K. In the inset the reduced partial DPS, $g(E)/(E^2)$, is shown in units of $10^{-4}/\text{meV}^3$ with the low energy fit, between 0 and 4 meV, for the Debye levels, indicated by the same line style. The Debye level is proportional to the mass of the element and hence different for Fe and Sb.

TABLE II: The transverse, longitudinal and average sound velocities, in m/s.

Direction	TA1	TA2	LA	average v_s
[100]	3181	3649	5123	3703
[010]	2249	3700	5473	2975
[001]	2306	3189	4666	2811
[110]	2754	3108	5285	3243
[011]	2850	3213	4420	3281

ual transition from diamagnetic to paramagnetic behavior and the activation of charge carriers, see experimental data in Fig. 2. This anomalous hardening is a further indication of strong coupling between lattice and electronic degrees of freedom. The qualitative temperature dependence reported herein is not be affected by the modelling problems related to the use of a sintered polycrystalline sample, however, measurements on single crystal will be highly desirable as soon as large enough samples become available, in order to quantitatively verify the impact of the coupling of electronic and lattice degrees of freedom on specific elastic moduli.

The elastic constants with and without inclusion of spin orbit interaction were also calculated, directly using perturbation theory (wrt strain) as described in Ref.⁴³. The elastic constant tensor components c_{ij} reported in Tab. III are for relaxed ions. Note that the tensor was symmetrized. Experimental or other theoretical results are not available for a direct comparison with the calculated elastic constants c_{ij} in Fig. 7. The measurements of c_{44} and the value obtained at low T are consistent with the calculated values, see Tab. III, but a precise compar-

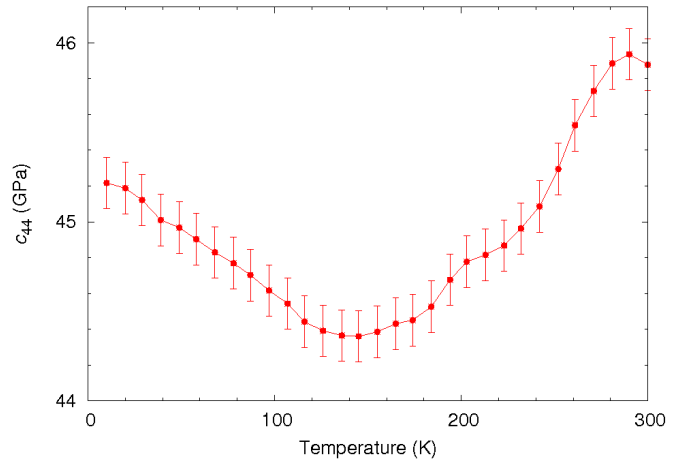


FIG. 7: Temperature dependence of the shear modulus, c_{44} , in a sintered polycrystalline sample of FeSb_2 .

ison will require measurements on a single crystal. We can also see that the inclusion of effects due to spin orbit interaction has as consequence to increase the values of all c_{ij} , except for c_{44} , c_{55} and c_{66} where values are relatively higher in the absence of spin orbit coupling.

TABLE III: Elastic constants of FeSb_2 with and without contribution from spin orbit interaction (SOI) in Voigt notation and in units of GPa.

α	without SOI						with SOI					
	1	2	3	4	5	6	1	2	3	4	5	6
1	225.8	64.3	72.1				265	68.5	85			
2	64.3	258.1	32.0				68.5	307	49.5			
3	72.1	32.0	186.5				85	49.5	252			
4				45						36		
5					89						70	
6						116						79

The speeds of sound extracted from the elastic constants are in good agreement with the values reported in Tab.II, and agree reasonably well with experiments.

3. *Specific heat.* Using the calculated phonon frequencies and density of states, the temperature dependence of specific heat C_v was computed and compared with measurements. The theoretical and experimental results are illustrated in Fig. 8 and are in excellent agreement. The curves evolves smoothly at low temperatures following the Debye model $C_v \sim (\frac{T}{\Theta_D})^3$ and approaches the Dulong-Petit limit $C_v \sim 75 \text{ J mol}^{-1} \text{ K}^{-1}$ at high temperatures.

E. Electron-phonon coupling

Our results for the phonon dispersion along several symmetry directions together with the corresponding

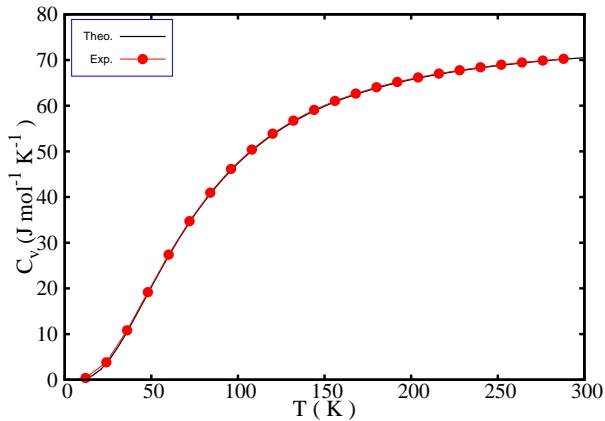


FIG. 8: Plot of the specific heat of $FeSb_2$ (full line) as function of temperature. Results are in very good agreement with measurements (dotted line).

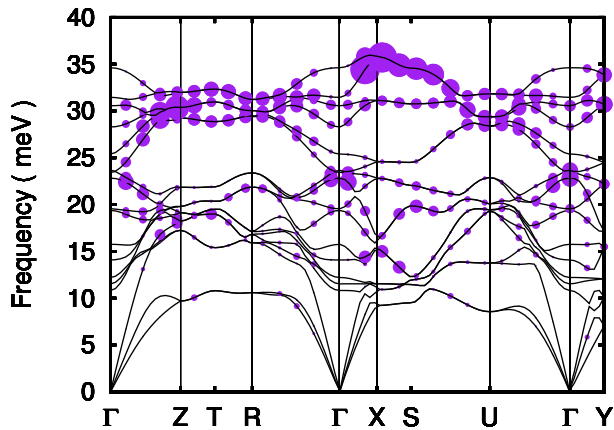


FIG. 9: Calculated phonon spectrum of $FeSb_2$ along the high symmetry lines of the Brillouin zone. The points size indicates the line broadening due to electron phonon coupling.

linewidth broadening due to electron phonon coupling are displayed in Fig. 9. The energy range of phonon modes extending from 0 up to 35 meV as well as the trend of the electron phonon coupling along the different branches are consistent with a recent direct experimental measurement using inelastic neutron scattering⁴⁴. Among the various areas explored in the first Brillouin zone we note that the stronger electron phonon couplings are observed in the vicinity of the $Z[0,0,0.5]$, $X[0.5,0,0]$ and $S[0.5,0.5,0]$ points, for the optical modes. As shown in Fig. 6, the optical modes are largely dominated by contribution from Fe ions. The maximum value of the linewidth broadening is achieved at X. The Eliashberg spectral function $\alpha^2 F(\omega)$ is shown in Fig. 10. The value of the dimensionless electron-phonon coupling strength defined through $\lambda = 2 \int \alpha^2 F(\omega) d\omega / \omega$ is 0.24, this value is fairly low compared to calculated values for simple metals⁴⁵. Since no additional broadening due to anharmonic effects can be expected at such low temperatures, our study reveals that the observed electron phonon interaction may

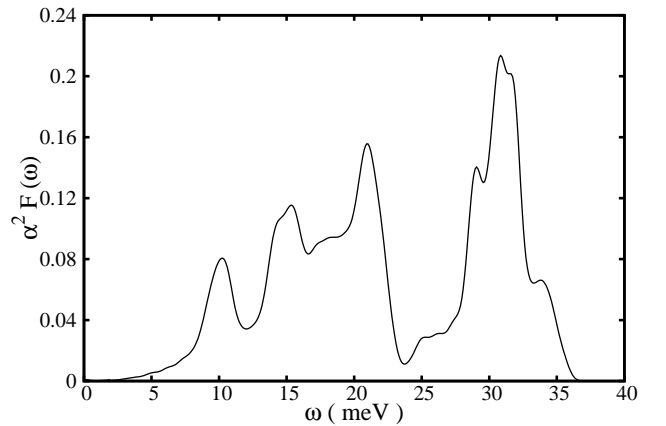


FIG. 10: Electron-phonon spectral function for $FeSb_2$. The results are based on the calculated frequencies.

play a major role in the transport properties. This is consistent with recent measurements⁴⁶ which have shown a significant increase of linewidths broadening with temperature in the range 0 - 40 K.

IV. CONCLUSIONS

We have analyzed the vibrational, thermoelectric and magnetic properties of the semiconductor $FeSb_2$ through nuclear inelastic scattering, ultrasound experiments, and modeling using DFT. The GGA was sufficient to reliably treat the full set of physical properties on which we focused.

The theoretical approaches provide a valuable insight into the link between the electronic structure and the thermoelectric properties. We have shown that the contribution of the electrons to the thermal conductivity is not the predominant term in the huge negative value of Seebeck coefficient S experimentally observed at low temperature. Our analysis shows that a local electronic structure picture can explain the position, but not the large amplitude of the $T \sim 12$ K peak in S , suggesting the possible presence of phonon drag effects²⁰ as it was already found in pure semiconductors silicon^{47,48} and germanium^{49,50}.

The correlation between the magnetic susceptibility and the electrical resistivity was highlighted. It can be seen in the behavior of the resistivity when raising temperature. In the low spin state diamagnetic phase the value of the resistivity is four orders of magnitude larger than the value in the paramagnetic high spin state at room temperature. This significant increase of the electrical conductivity in the paramagnetic region agrees with Goodenough's hypothesis⁵¹ that thermal excitation favors the population of the less localized orbitals rather than more localized orbitals. Therefore the magnetic susceptibility can be explained either by a low spin to high spin transition, or as mentioned above by a thermally activated Pauli susceptibility. Further band structure calculations

and experiments are however necessary to clarify this issue. For instance, in the band structure calculation the orientation of localized and non-localized orbitals should be known.

The combined experimental and theoretical study has enabled a direct comparison of measurements and calculations. Although differences were observed between the measured and calculated sound velocities, a very good agreement was obtained for the partial density of phonon states and the temperature dependence of heat capacity. The correlation between the temperature evolution of the shear moduli and the transition from diamagnetic to paramagnetic behavior is emphasized. We have also studied the effects due to electron phonon coupling. The linewidth broadening along high symmetry directions were analyzed. The stronger electron-phonon interaction was observed for optical modes of Fe around the Z, X and S points. This suggests significant mode asymmetry. Since there are no experimental data available yet, our ab-initio estimations of the linewidth broadening due to electron-phonon interaction presented here, may have potential practical implications. They can provide a basis for addressing a detailed experimental study of the effects of electron phonon coupling in the thermo-

electric properties of FeSb₂. Inelastic scattering experiments could more deeply investigate this domain, and work is ongoing in this direction. Studies led until now do not reveal a credible and conclusive explanation of the fascinating low temperature behavior of FeSb₂.

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